Yue Xu

List of Publications by Year
in descending order

34 papers	274 citations	933447 10 h-index	940533 16 g-index
34 all docs	34 docs citations	34 times ranked	237 citing authors

#	Article	IF	Citations
1	A CMOS Front-End Hall Sensor Microsystem for Linear Magnetic Field Measurement With Best Tradeoff Between Sensitivity and SNR. IEEE Transactions on Instrumentation and Measurement, 2022, 71, 1-8.	4.7	4
2	An integrated front-end vertical hall magnetic sensor fabricated in 0.18 Î¼m low-voltage CMOS technology. Journal of Semiconductors, 2022, 43, 032402.	3.7	2
3	Sensitivity Improvement of a Fully Symmetric Vertical Hall Device Fabricated in 0.18 Î¼m Low-Voltage CMOS Technology. IEEE Journal of the Electron Devices Society, 2021, 9, 820-826.	2.1	1
4	A compact time-to-amplitude converter for single-photon time-of-flight measurement. Journal of Modern Optics, 2021, 68, 463-470.	1.3	0
5	Compact SPAD pixels with fast and accurate photon counting in the analog domain. Journal of Semiconductors, 2021, 42, 052402.	3.7	4
6	A Time-to-Amplitude Converter With High Impedance Switch Topology for Single-Photon Time-of-Flight Measurement. IEEE Access, 2021, 9, 16672-16678.	4.2	2
7	A Compact High-Speed Active Quenching and Recharging Circuit for SPAD Detectors. IEEE Photonics Journal, 2020, 12, 1-8.	2.0	15
8	Reducing dark count of single-photon avalanche diode detector with polysilicon field plate. Wuli Xuebao/Acta Physica Sinica, 2020, 69, 148501.	0.5	2
9	A Current-Mode CMOS Hall Sensor Microsystem based on Four-Phase Current Spinning Technique. , 2019, , .		1
10	A Compact SPAD Pixel With Active Quenching And Recharging. , 2019, , .		0
11	Behavioral Modeling of Photon Arrival Time for Time-of-Flight Measurement Circuit Simulation. IEEE Photonics Journal, 2019, 11, 1-9.	2.0	2
12	A Simple Analytic Modeling Method for SPAD Timing Jitter Prediction. IEEE Journal of the Electron Devices Society, 2019, 7, 261-267.	2.1	17
13	Deep Sub-60 mV/decade Subthreshold Swing in AlGaN/GaN FinMISHFETs with M-Plane Sidewall Channel. IEEE Transactions on Electron Devices, 2019, 66, 1699-1703.	3.0	14
14	Improved Performance of CMOS Terahertz Detectors by Reducing MOSFET Parasitic Capacitance. IEEE Access, 2019, 7, 9783-9789.	4.2	11
15	An Analytical Geometry Optimization Model for Current-Mode Cross-Like Hall Plates. Sensors, 2019, 19, 2490.	3.8	5
16	Dual-frequency CMOS terahertz detector with silicon-based plasmonic antenna. Optics Express, 2019, 27, 23250.	3.4	15
17	A novel compact analog counter for high density SPAD array imagers. Microelectronics Journal, 2018, 74, 43-48.	2.0	5
18	Performance Improvement and Sub-60 mV/Decade Swing in AlGaN/GaN FinFETs by Simultaneous Activation of 2DEG and Sidewall MOS Channels. IEEE Transactions on Electron Devices, 2018, 65, 915-920.	3.0	15

#	Article	IF	Citations
19	An accurate behavioral model for single-photon avalanche diode statistical performance simulation. Superlattices and Microstructures, 2018, 113, 635-643.	3.1	10
20	A new modeling and simulation method for important statistical performance prediction of single photon avalanche diode detectors. Semiconductor Science and Technology, 2016, 31, 065024.	2.0	38
21	A 10-bit 100 MS/s CMOS current-steering DAC. , 2016, , .		4
22	Performance prediction of four-contact vertical Hall-devices using a conformal mapping technique. Journal of Semiconductors, 2015, 36, 124006.	3.7	4
23	A Monolithic CMOS Magnetic Hall Sensor with High Sensitivity and Linearity Characteristics. Sensors, 2015, 15, 27359-27373.	3.8	21
24	A novel Hall dynamic offset cancellation circuit based on four-phase spinning current technique. , 2015, , .		1
25	Fully integrated high density SPAD array detector. , 2014, , .		0
26	Study of charge loss mechanisms for nano-sized localized trapping SONOS memory devices. Solid-State Electronics, 2014, 91, 118-122.	1.4	4
27	An 8-level 3-bit cell programming technique in NOR-type nano-scaled SONOS memory devices. Microelectronics Reliability, 2014, 54, 331-334.	1.7	0
28	An improved multilevel cell programming technique for 4-bits/cell localized trapping SONOS memory devices. Microelectronics Reliability, 2013, 53, 118-122.	1.7	2
29	Monolithic Hâ€bridge brushless DC vibration motor driver with a highly sensitive Hall sensor in 0.18 Î¼m complementary metalâ€oxide semiconductor technology. IET Circuits, Devices and Systems, 2013, 7, 204-210.	1.4	9
30	A Highly Sensitive CMOS Digital Hall Sensor for Low Magnetic Field Applications. Sensors, 2012, 12, 2162-2174.	3.8	31
31	A 3-bit multilevel cell programming method in nitride memory devices. , 2012, , .		0
32	A simplified compact model of miniaturized cross-shaped CMOS integrated Hall devices. Journal of Semiconductors, 2012, 33, 084005.	3.7	2
33	Comparison of local programming method for multi-bit/level 90nm SONOS memory. , 2012, , .		0
34	An Improved Equivalent Simulation Model for CMOS Integrated Hall Plates. Sensors, 2011, 11, 6284-6296.	3.8	33